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FDC658P

Single P-Channel, Logic Level, PowerTrench™ MOSFET

General Description

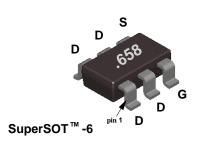
This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

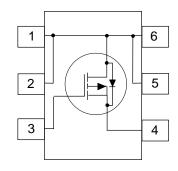
These devices are well suited for notebook computer applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- Low gate charge (8nC typical).
- High performance trench technology for extremely low R_{DS/ONI}.
- SuperSOTTM-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).







Absolute Maximum Ratings

$T_A = 25^{\circ}C$ unless	otherwise note
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Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage - Continuous		±20	V
I _D	Drain Current - Continuous	(Note 1a)	-4	А
	- Pulsed		-20	
P_{D}	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to 150	
THERMA	AL CHARACTERISTICS			•
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)		78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)		30	°C/W

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS			•	•	•	•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_D = -250 \mu\text{A}$, Referenced	to 25 °C		-22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, \ V_{GS} = 0 \text{ V}$				-1	μΑ
			T _J = 55 °C			-10	μΑ
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	1			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHARA	CTERISTICS (Note 2)			I.	·		u .
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1	-1.7	-3	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold VoltageTemp.Coefficient	$I_D = -250 \mu\text{A}$, Referenced	to 25 °C		4.1		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_{D} = -4.0 \text{ A}$			0.041	0.05	Ω
()			T _J = 125 °C		0.058	0.08	
		$V_{GS} = -4.5 \text{ V}, I_D = -3.4 \text{ A}$	1 -		0.06	0.075	
D(on)	On-State Drain Current	$V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$		-20			Α
9 _{FS}	Forward Transconductance	$V_{DS} = -5V, I_{D} = -4 A$			9		S
DYNAMIC CI	HARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}, \ V_{GS} = 0 \text{ V},$			750		pF
Coss	Output Capacitance	f = 1.0 MHz			220		pF
C _{rss}	Reverse Transfer Capacitance				100		pF
SWITCHING	CHARACTERISTICS (Note 2)						
t _{D(on)}	Tum - On Delay Time	$V_{DD} = -15 \text{ V}, \ I_{D} = -1 \text{ A},$			12	22	ns
ţ	Turn - On Rise Time	$V_{\text{GS}} = \text{-10 V}, \ R_{\text{GEN}} = 6\Omega$			14	25	ns
D(off)	Turn - Off Delay Time				24	38	ns
f	Turn - Off Fall Time				16	27	ns
Q_g	Total Gate Charge	$V_{DS} = -15 \text{ V}, \ I_{D} = -4.0 \text{ A},$			8	12	nC
Q_{gs}	Gate-Source Charge	V _{GS} = -5 V			1.8		nC
Q_{gd}	Gate-Drain Charge				3		nC
DRAIN-SOUI	RCE DIODE CHARACTERISTICS						
S	Continuous Source Diode Current					-1.3	Α
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A}$ (No	ite 2)		-0.76	-1.2	V

Notes

^{1.} $R_{\mu\mu}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\mu\nu}$ is guaranteed by design while $R_{\mu\nu}$ is determined by the user's board design.

a. 78°C/W when mounted on a 1 in² pad of 2oz Cu on FR-4 board.

b. 156°C/W when mounted on a minimum pad of 2oz Cu on FR-4 board.

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

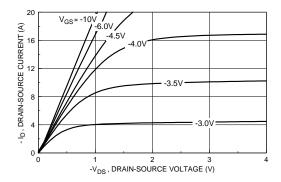


Figure 1. On-Region Characteristics.

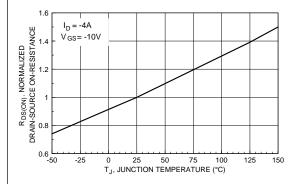


Figure 3. On-Resistance Variation with Temperature.

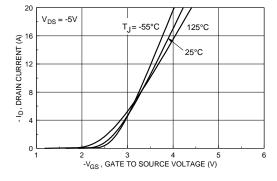


Figure 5. Transfer Characteristics.

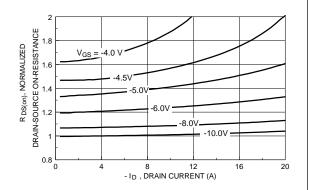


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

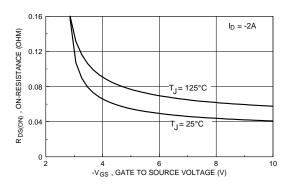


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

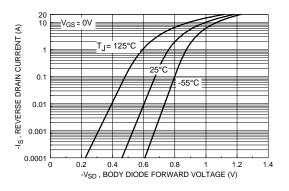


Figure 6. Body Diode Forward Voltage

Variation with Source Current
and Temperature.

Typical Electrical Characteristics (continued)

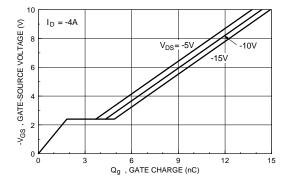


Figure 7. Gate Charge Characteristics.

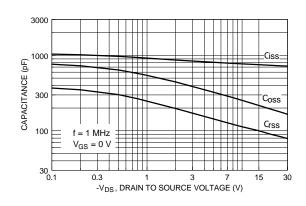


Figure 8. Capacitance Characteristics.

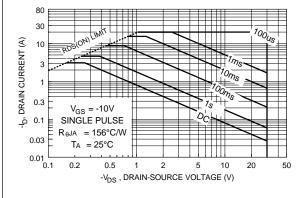


Figure 9. Maximum Safe Operating Area.

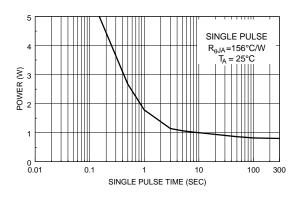


Figure 10. Single Pulse Maximum Power Dissipation.

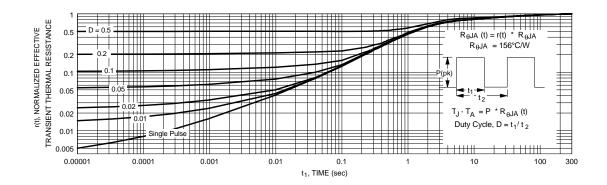


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.

Transient thermal response will change depending on the circuit board design.

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